

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

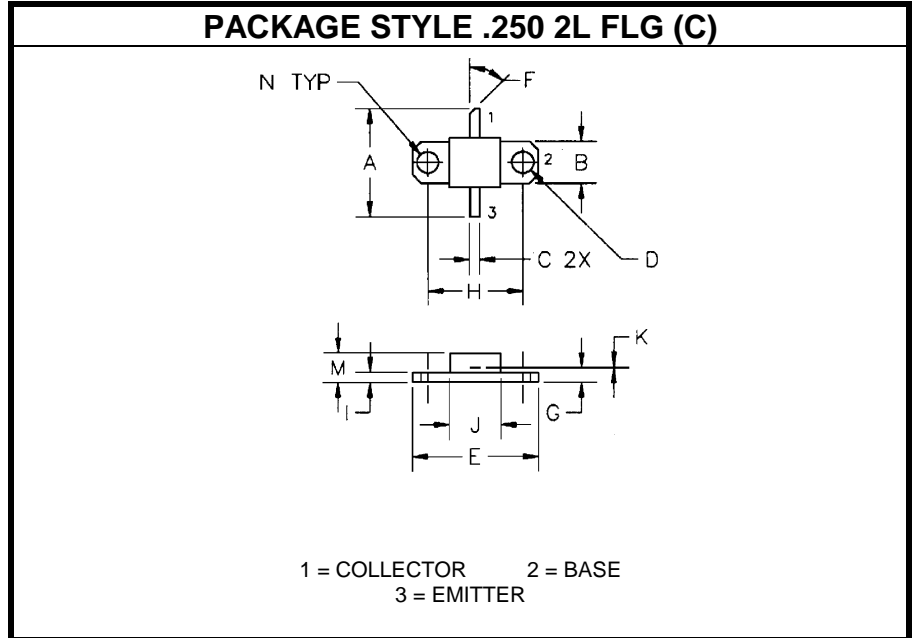
The **MRAL2023-3** is a Common Base Device Designed for class C Amplifier Applications in L-Band FM Microwave Links.

FEATURES INCLUDE:

- Gold Metallization
- Emitter Ballasting
- Input Matching

MAXIMUM RATINGS

I_C	0.5 A
V_{CES}	40 V
P_{DISS}	10 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	16°C/W


CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 20\text{ mA}$	40			V
BV_{EBO}	$I_E = 1.0\text{ mA}$	3.5			V
I_{CBO}	$V_{CB} = 22\text{ V}$			1.0	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 200\text{ mA}$	10			---
C_{OB}	$V_{CB} = 22\text{ V}$ $f = 1.0\text{ MHz}$			5	pF
P_G η_C	$V_{CE} = 22\text{ V}$ $P_{OUT} = 3.0\text{ W}$ $f = 2000\text{ to }2300\text{ MHz}$	8.0	8.5 45		dB %